Lonten N-channel 100V, 65A, 8.5mΩ Power MOSFET

Description

These N-Channel enhancement mode power field effect transistors are using split gate trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and with stand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

- 100V,65A,$R_{DS(ON).max}$=8.5mΩ@V_{GS}=10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green device available

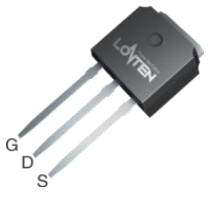
Applications

- Motor Drives
- UPS
- DC-DC Converter

Product Summary

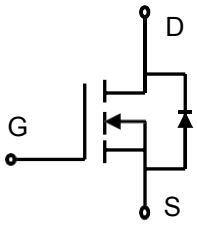
V_{DSS}	100V
$R_{DS(on).max}$@ V_{GS}=10V	8.5mΩ
I_D	65A

Pin Configuration



TO-251

TO-252



N-Channel MOSFET

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	V
Continuous drain current (T_C = 25°C) [1]	I_D	65	A
Continuous drain current (T_C = 100°C) [1]		41	A
Pulsed drain current [2]	I_{DM}	240	A
Gate-Source voltage	V_{GSS}	±20	V
Avalanche energy, single pulse [3]	E_{AS}	110	mJ
Power Dissipation (T_C = 25°C)	P_D	96	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.3	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	68	°C/W

Package Marking and Ordering Information

Device	Device Package	Marking
LSGG10R085W3	TO-252	SGG10R085W3
LSGH10R085W3	TO-251	SGH10R085W3

Electrical Characteristics T_J = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=250uA	100	---	---	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.4	1.8	2.2	V
Drain-source leakage current	I_{DSS}	V_{DS}=100V, V_{GS}=0V, T_J = 25°C	---	---	1	μA
		V_{DS}=80V, V_{GS}=0V, T_J = 125°C	---	---	10	μA
Gate leakage current, Forward	I_{GSSF}	V_{GS}=20 V, V_{DS}=0 V	---	---	100	nA
Gate leakage current, Reverse	I_{GSSR}	V_{GS}=-20 V, V_{DS}=0 V	---	---	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=30 A	---	7.0	8.5	mΩ
Drain-source on-state resistance		V_{GS}=4.5 V, I_D=20 A	---	8.8	10.5	mΩ
Forward transconductance	g_{fs}	V_{DS} =5V , I_D=30A	---	112	---	S
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS} = 50 V, V_{GS} = 0 V, F = 1MHz	---	2630	---	pF
Output capacitance	C_{oss}		---	453	---	
Reverse transfer capacitance	C_{rss}		---	36	---	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 50V,V_{GS}=10V, I_D = 30A	---	10.5	---	ns
Rise time	t_r		---	63	---	
Turn-off delay time	$t_{d(off)}$		---	30	---	
Fall time	t_f		---	96	---	
Gate resistance	R_g	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	1.1	---	Ω
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DS}=50 V, I_D=50A, V_{GS}= 10 V	---	10.2	---	nC
Gate to drain charge	Q_{gd}		---	6.6	---	
Gate charge total	Q_g		---	45	---	
Drain-Source diode characteristics and Maximum Ratings						
Continuous Source Current	I_S	V_G=V_D=0 V, Force Current	---	---	65	A
Pulsed Source Current	I_{SM}		---	---	240	A
Diode Forward Voltage[4)]	V_{SD}	V_{GS}=0V, I_S=30A, T_J=25℃	---	0.95	1.3	V
Reverse Recovery Time	t_{rr}	I_S=30A, di/dt=100A/us, T_J=25℃	---	65	---	ns
Reverse Recovery Charge	Q_{rr}		---	104	---	nC

Notes:

1: The maximum junction current rating is package limited.

2: Repetitive Rating: Pulse width limited by maximum junction temperature.

3: V_{DD}=50V, V_{GS}=10V, L=0.5mH, I_{AS}=21A, R_G=25Ω, Starting T_J=25℃.

4: Pulse Test：Pulse Width ≤300 μ s, Duty Cycle≤2%.

Electrical Characteristics Diagrams

Figure 1. Typ. Output Characteristics

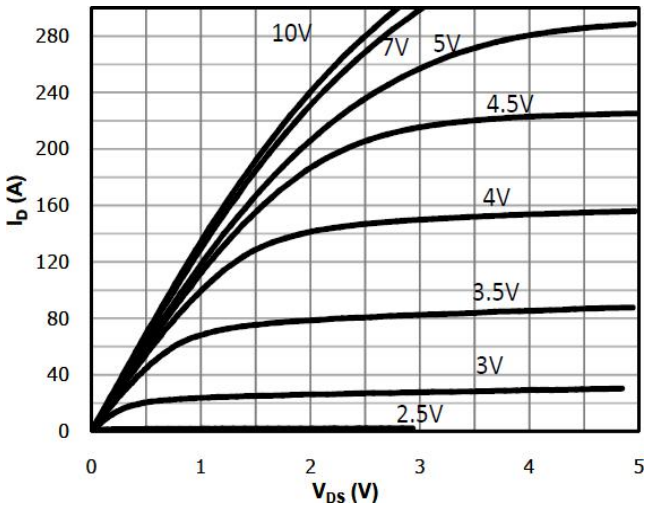


Figure 2. Transfer Characteristics

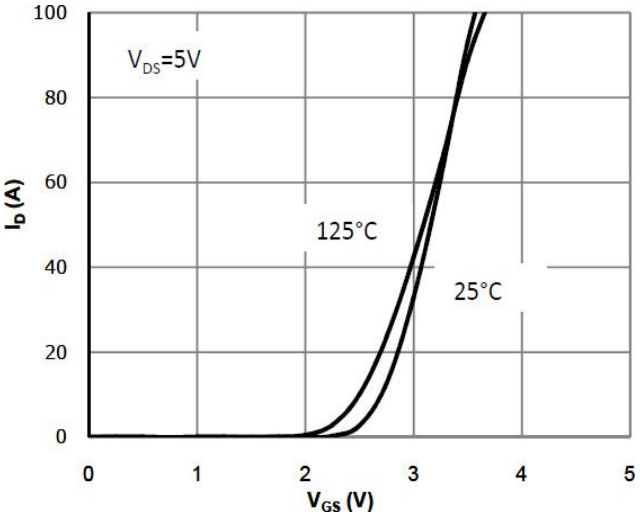


Figure 3. Capacitance Characteristics

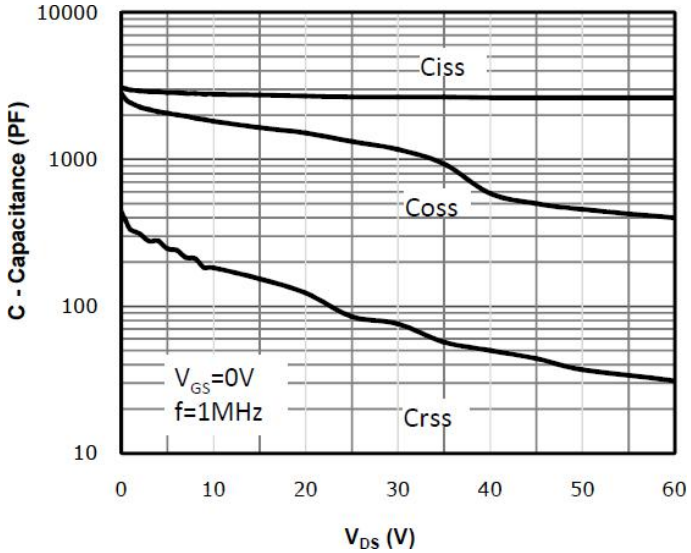


Figure 4. Gate Charge Waveform

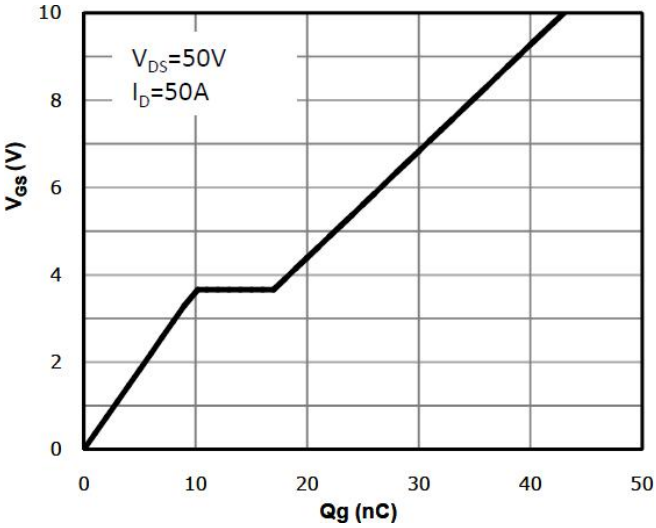


Figure 5. Body-Diode Characteristics

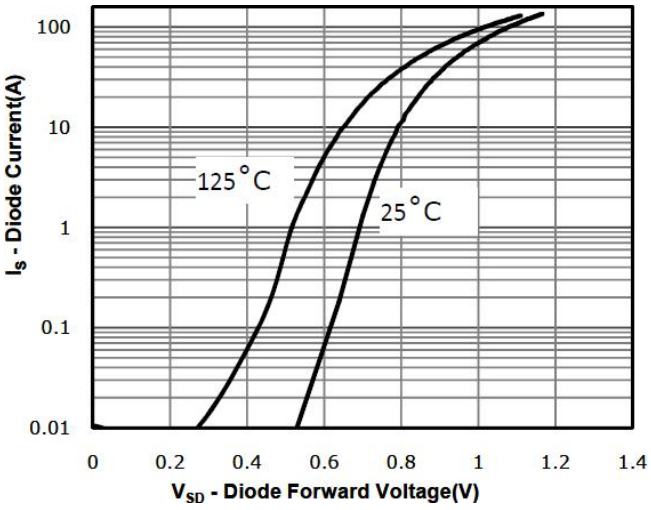


Figure 6. Rdson-Drain Current

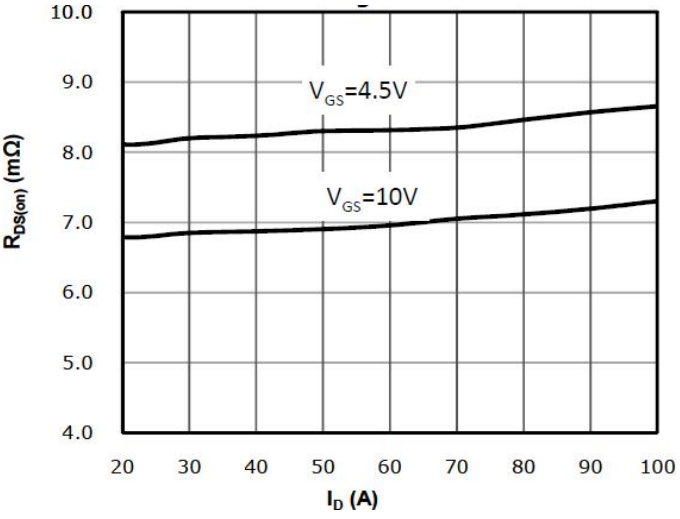


Figure 7. Rdson-Junction Temperature(℃)

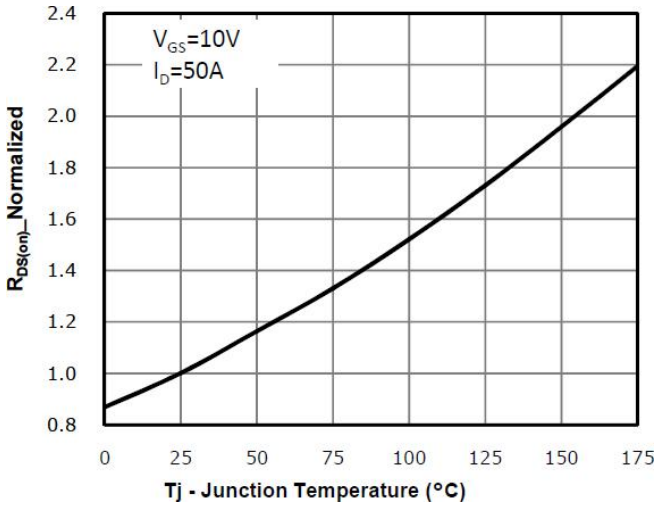


Figure 8. Maximum Safe Operating Area

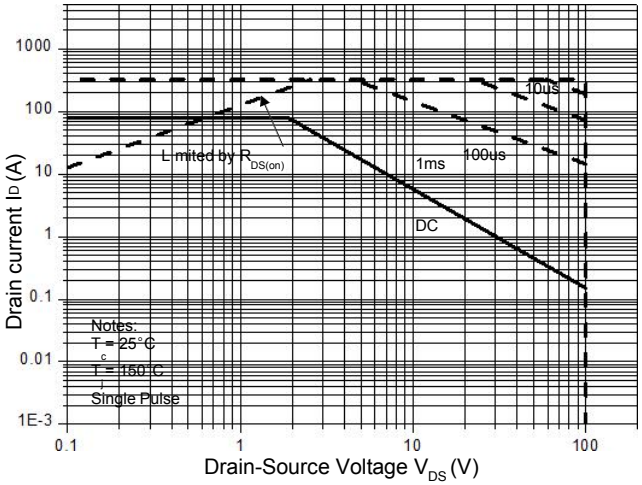
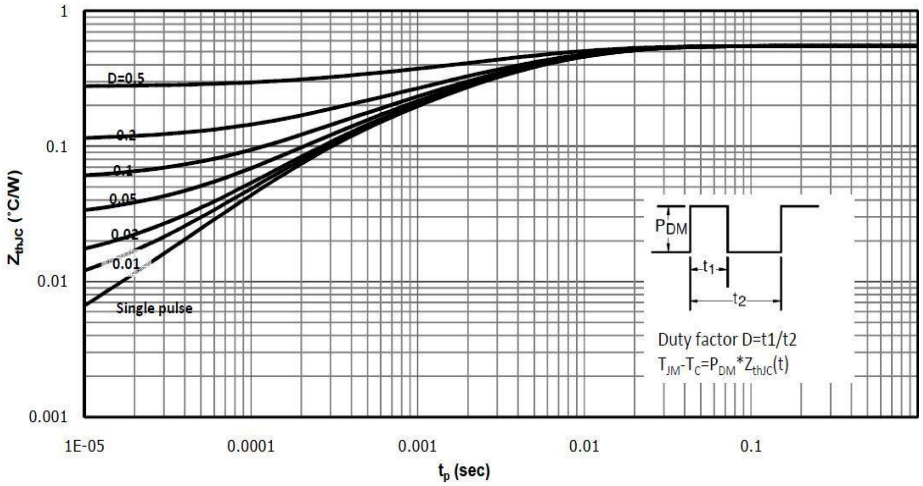


Figure 9. Normalized Maximum Transient Thermal Impedance (RthJC)



Test Circuit & Waveform

Figure 8. Gate Charge Test Circuit & Waveform

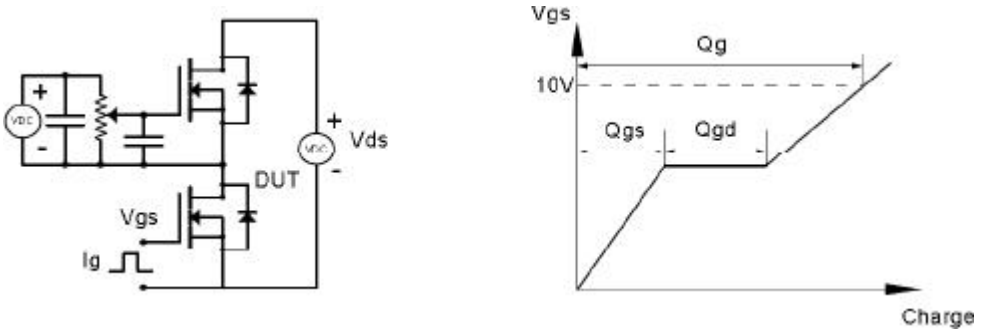


Figure 9. Resistive Switching Test Circuit & Waveforms

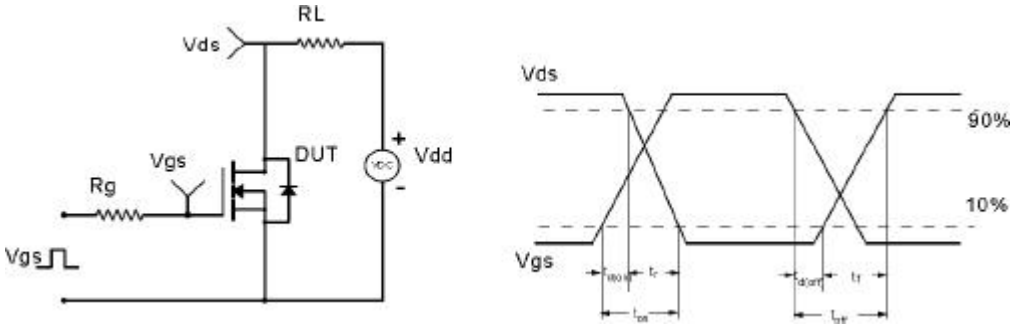


Figure 10. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

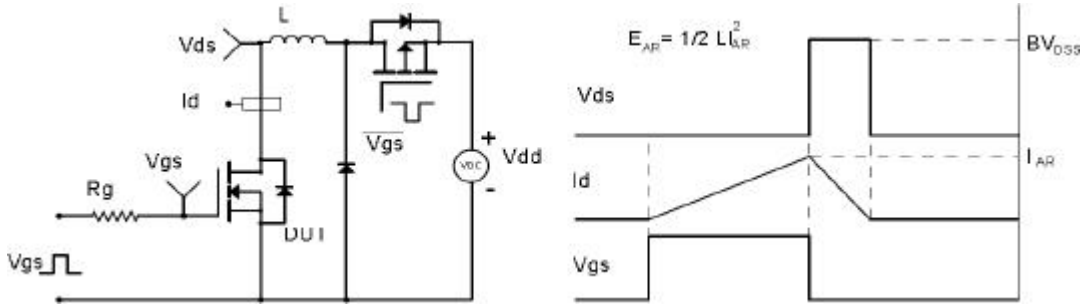
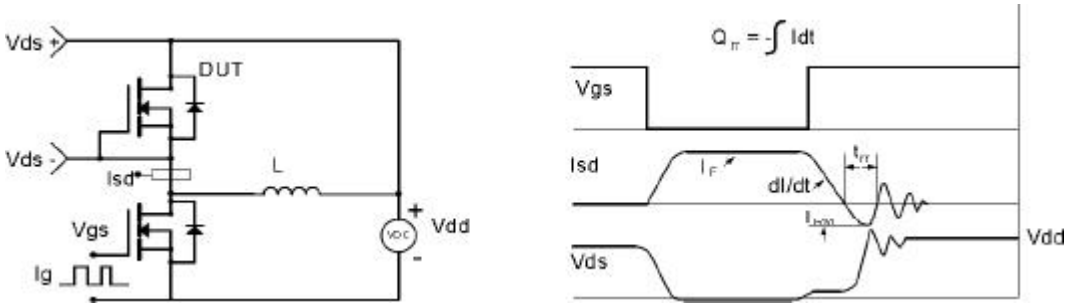
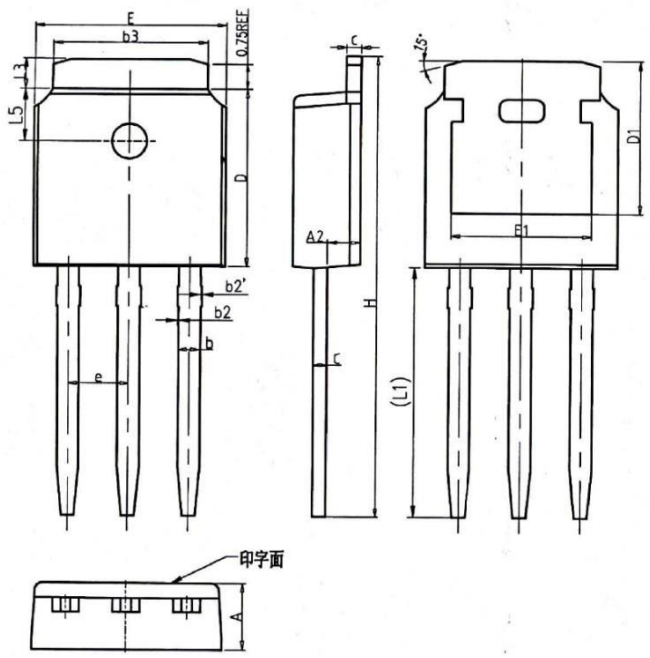


Figure 11. Diode Recovery Circuit & Waveform

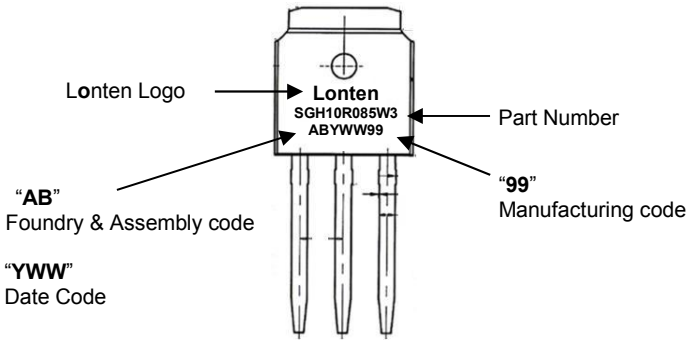


Mechanical Dimensions for TO-251

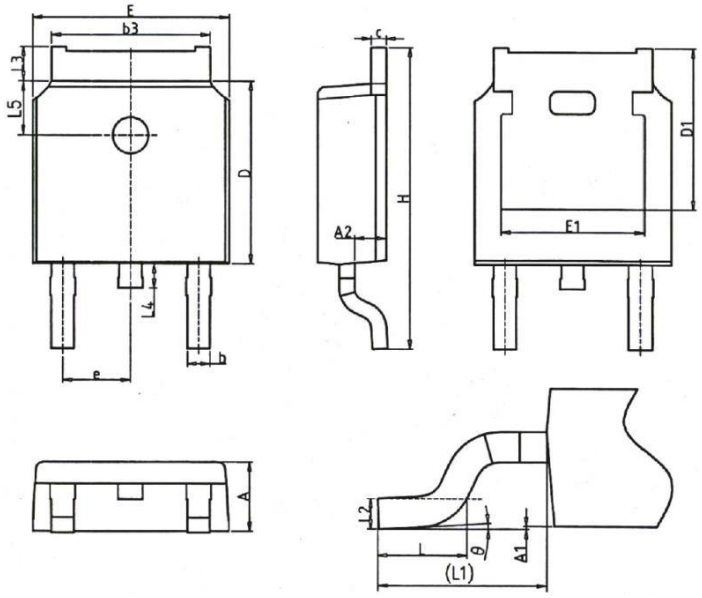


COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.20	2.30	2.38	0.087	0.091	0.094
A2	0.97	1.07	1.17	0.038	0.042	0.046
b	0.68	0.78	0.90	0.027	0.031	0.035
b2	0.00	0.04	0.10	0.000	0.002	0.004
b2'	0.00	0.04	0.10	0.000	0.002	0.004
b3	5.20	5.33	5.46	0.205	0.210	0.215
c	0.43	0.53	0.61	0.017	0.021	0.024
D	5.98	6.10	6.22	0.235	0.240	0.245
D1	5.30REF			0.209REF		
E	6.40	6.60	6.73	0.252	0.260	0.265
E1	4.63	-	-	0.182	-	-
e	2.286BSC			0.090BSC		
H	16.22	16.52	16.82	0.639	0.650	0.662
L1	9.15	9.40	9.65	0.360	0.370	0.380
L3	0.88	1.02	1.28	0.035	0.040	0.050
L5	1.65	1.80	1.95	0.065	0.071	0.077

TO-251 Part Marking Information

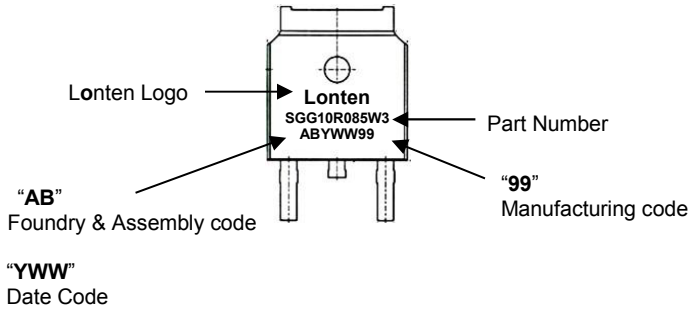


Mechanical Dimensions for TO-252



COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.20	2.30	2.38	0.087	0.091	0.094
A1	0.00	-	0.20	0.000	-	0.008
A2	0.97	1.07	1.17	0.038	0.042	0.046
b	0.68	0.78	0.90	0.027	0.031	0.035
b3	5.20	5.33	5.46	0.205	0.210	0.215
c	0.43	0.53	0.61	0.017	0.021	0.024
D	5.98	6.10	6.22	0.235	0.240	0.245
D1	5.30REF			0.209REF		
E	6.40	6.60	6.73	0.252	0.260	0.265
E1	4.63	-	-	0.182	-	-
e	2.286BSC			0.090BSC		
H	9.40	10.10	10.50	0.370	0.398	0.413
L	1.38	1.50	1.75	0.054	0.059	0.069
L1	2.90REF			0.114REF		
L2	0.51BSC			0.020BSC		
L3	0.88	-	1.28	0.035	-	0.050
L4	0.50	-	1.00	0.020	-	0.039
L5	1.65	1.80	1.95	0.065	0.071	0.077
θ	0°	-	8°	0°	-	8°

TO-252 Part Marking Information



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